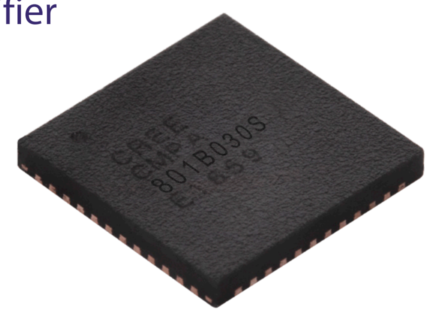
CMPA801B030S

7.9 - 11.0 GHz, 40 W, Packaged GaN MMIC Power Amplifier



Description

Cree's CMPA801B030S is a packaged, 40W HPA utilizing Cree's high performance, 0.15um GaN on SiC production process. The CMPA801B030S operates from 7.9-11.0 GHz and targets pulsed radar systems supporting both defense and commercial applications. With 2 stages of gain, this high performance amplifier provides 20dB of large signal gain and 40% efficiency to support lower system DC power requirements and simplify system thermal management solutions. Packaged in a 7x7 mm plastic overmold QFN, the CMPA801B030S also supports reduced board space requirements and high-throughput manufacturing lines.

PN: CMPA801B030S
Package Type: 7x7 QFN

Typical Performance Over 7.9 - 11.0 GHz (T_C = 25˚C)

Parameter	8.0 GHz	8.5 GHz	9.0 GHz	10.0 GHz	11.0 GHz	Units
Small Signal Gain	28.2	27.5	27.1	24.6	24.0	dB
Output Power	39.3	45.9	48.9	42.3	40.7	W
Power Gain	19.9	20.6	21.0	20.3	20.1	dB
Power Added Efficiency	38.2	40.6	41.3	39.4	37.0	%

Notes: P_{IN} = 26 dBm, Pulse Width = 100 µs; Duty Cycle = 10%

Features

- Freq: 7.9 – 11.0 GHz
- Psat: 40 W
- PAE: 40%
- LS Gain: 20 dB
- 7x7 mm Overmold QFN
- Lower system costs
- Reduced board area

Note: Features are typical performance across frequency under 25°C operation. Please reference performance charts for additional details.

Applications

- Military pulsed radar
- Civil pulsed radar
- Satellite Communications

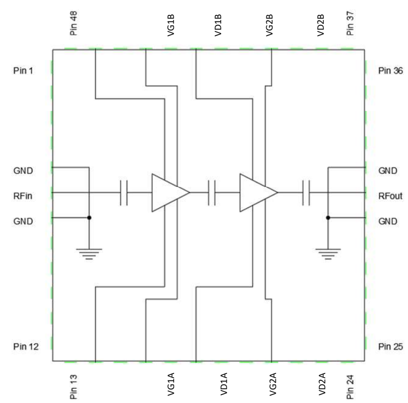


Figure 1.

RoHS COMPLIANT

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Absolute Maximum Ratings (not simultaneous) at 25˚C

Parameter	Symbol	Rating	Units	Conditions
Drain-source Voltage	V_{DSS}	84	VDC	25°C
Gate-source Voltage	V_{GS}	-8, +2	VDC	25°C
Storage Temperature	T_{STG}	-65, +150	˚C	
Maximum Forward Gate Current	I_G	12	mA	25°C
Maximum Drain Current	I_{DMAX}	6	A	
Soldering Temperature	T_S	260	˚C	

Electrical Characteristics (Frequency = 7.9 GHz to 11.0 GHz unless otherwise stated; T_C = 25˚C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics						
Gate Threshold Voltage	$V_{GS(TH)}$	-2.6	-	-1.6	V	V_{DS} = 10 V, I_D = 13 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-1.75	–	V_{DC}	V_{DD} = 28 V, I_{DQ} = 800 mA
Saturated Drain Current[1]	I_{DS}	–	4	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BD}	84	–	–	V	V_{GS} = -8 V, I_D = 13 mA
RF Characteristics[2,3]						
Small Signal Gain	$S21_1$	–	28.2	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA, Freq = 8.0 GHz
Small Signal Gain	$S21_2$	–	27.5	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA, Freq = 8.5 GHz
Small Signal Gain	$S21_3$	–	27.1	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA, Freq = 9.0 GHz
Small Signal Gain	$S21_4$	–	24.6	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA, Freq = 10.0 GHz
Small Signal Gain	$S21_5$	–	24.0	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA, Freq = 11.0 GHz
Output Power	P_{OUT1}	–	39.3	–	W	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 8.0 GHz
Output Power	P_{OUT2}	–	45.9	–	W	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 8.5 GHz
Output Power	P_{OUT3}	–	48.9	–	W	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 9.0 GHz
Output Power	P_{OUT4}	–	42.3	–	W	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 10.0 GHz
Output Power	P_{OUT5}	–	40.7	–	W	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 11.0 GHz
Power Added Efficiency	PAE_1	–	38	–	%	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 8.0 GHz
Power Added Efficiency	PAE_2	–	41	–	%	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 8.5 GHz
Power Added Efficiency	PAE_3	–	41	–	%	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 9.0 GHz
Power Added Efficiency	PAE_4	–	39	–	%	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 10.0 GHz
Power Added Efficiency	PAE_5	–	37	–	%	V_{DD} = 28 V, I_{DQ} = 800 mA, P_{IN} = 26 dBm, Freq = 11.0 GHz
Power Gain	G_P	–	21.0	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA
Input Return Loss	S11	–	-13	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA
Output Return Loss	S22	–	-10	–	dB	V_{DD} = 28 V, I_{DQ} = 800 mA
Output Mismatch Stress	VSWR	–	–	5 : 1	Ψ	No damage at all phase angles, V_{DD} = 28 V, I_{DQ} = 800 mA

Notes:
[1] Scaled from PCM data
[2] All data tested in CMPA801B030S-AMP1
[3] Pulse Width = 100 µs; Duty Cycle = 10%

Thermal Characteristics

Parameter	Symbol	Rating	Units	Conditions
Operating Junction Temperature	T_J	225	˚C	
Thermal Resistance, Junction to Case (packaged)[1]	$R_{\theta JC}$	2.5	˚C/W	100 µs, 10%, P_{DISS} = 25.5 W

Notes:
[1]Measured for the CMPA801B030S at P_{DISS} = 25.5 W

Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, PW = 100 us, DC = 10%, Pin = 26 dBm, T_{BASE} = +25 °C

Figure 1. Output Power vs Frequency as a Function of Temperature

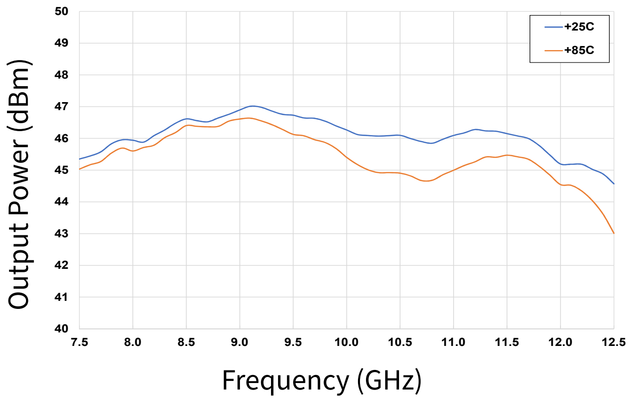


Figure 2. Output Power vs Frequency as a Function of Input Power

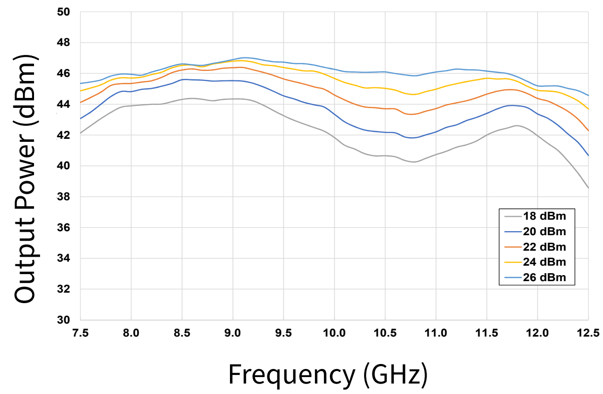


Figure 3. Power Added Eff. vs Frequency as a Function of Temperature

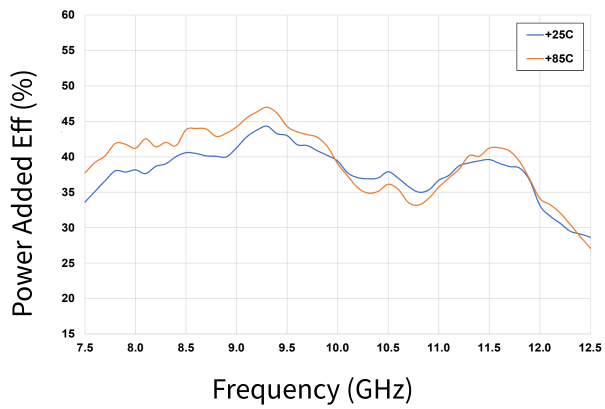


Figure 4. Power Added Eff. vs Frequency as a Function of Input Power

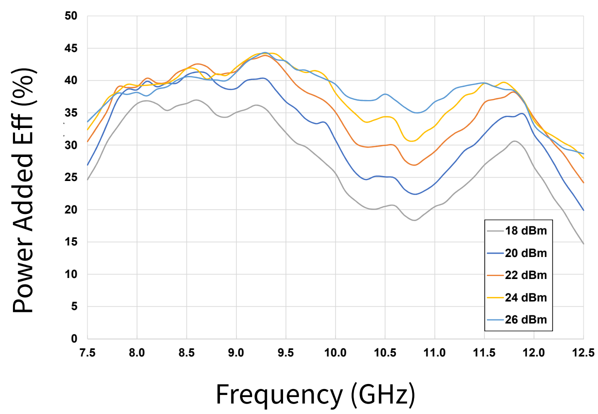


Figure 5. Drain Current vs Frequency as a Function of Temperature

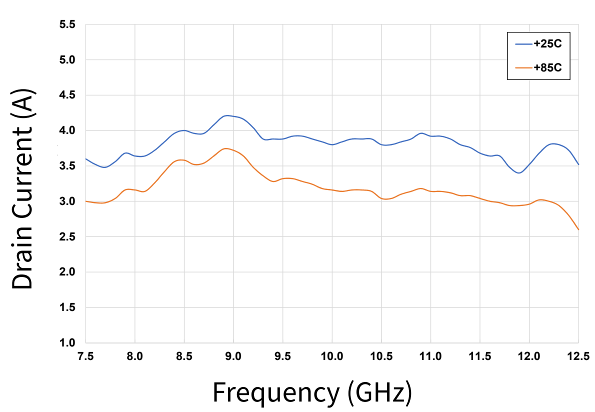
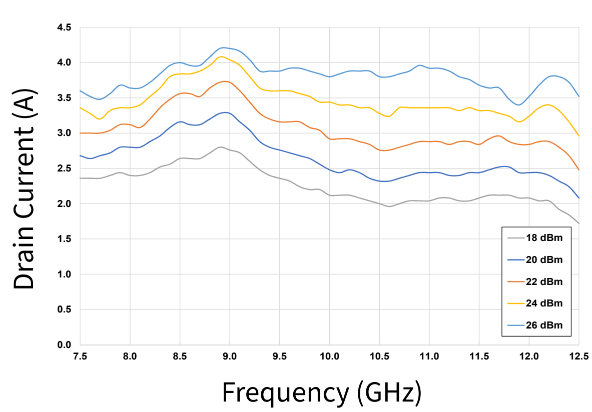


Figure 6. Drain Current vs Frequency as a Function of Input Power



Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, PW = 100 us, DC = 10%, Pin = 26 dBm, T_{BASE} = +25 °C

Figure 7. Output Power vs Frequency as a Function of VD

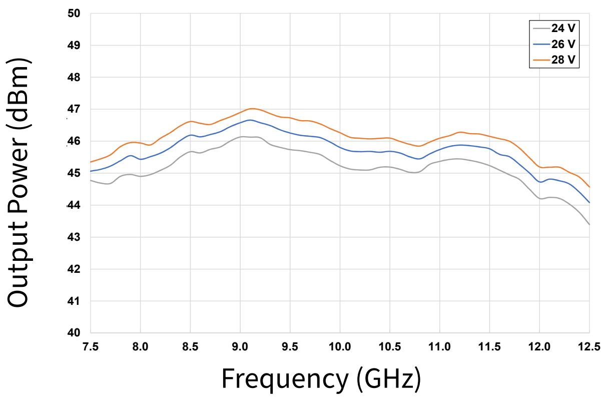


Figure 8. Output Power vs Frequency as a Function of IDQ

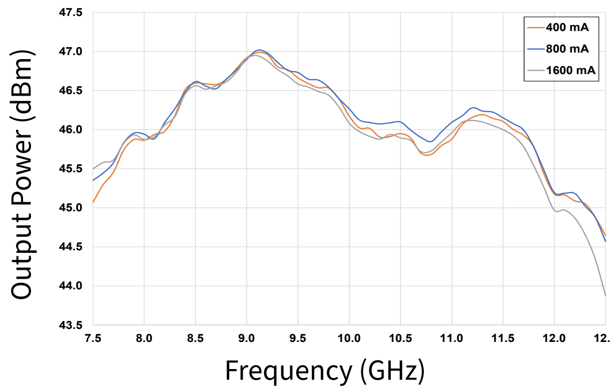


Figure 9. Power Added Eff. vs Frequency as a Function of VD

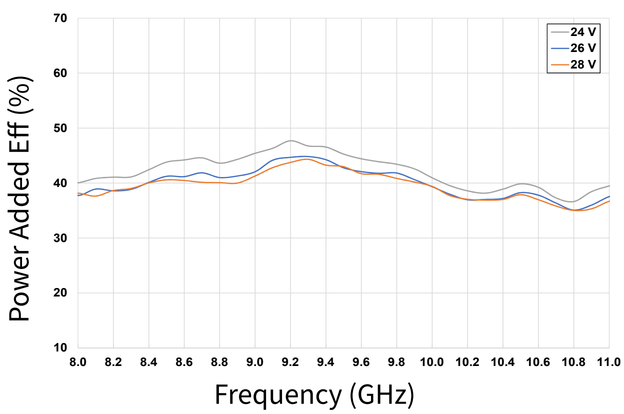


Figure 10. Power Added Eff. vs Frequency as a Function of IDQ

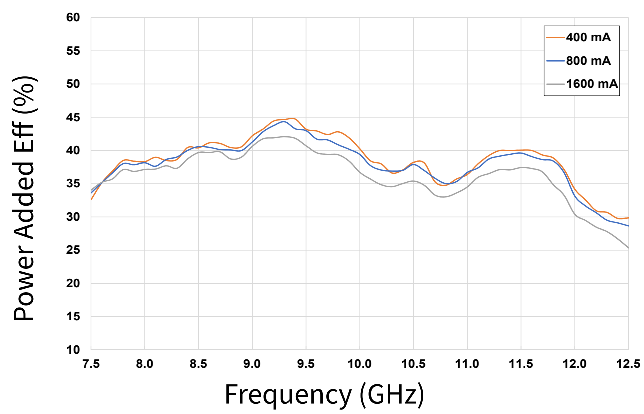


Figure 11. Drain Current vs Frequency as a Function of VD

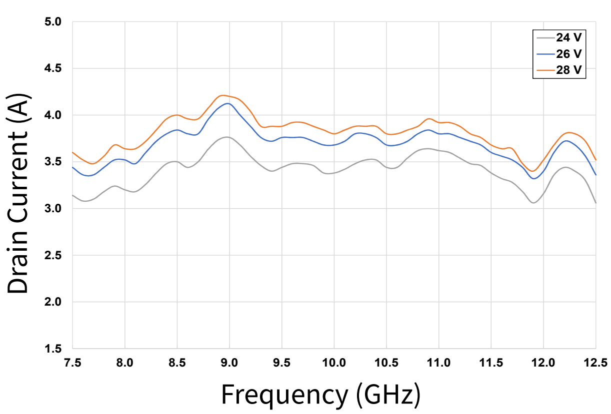
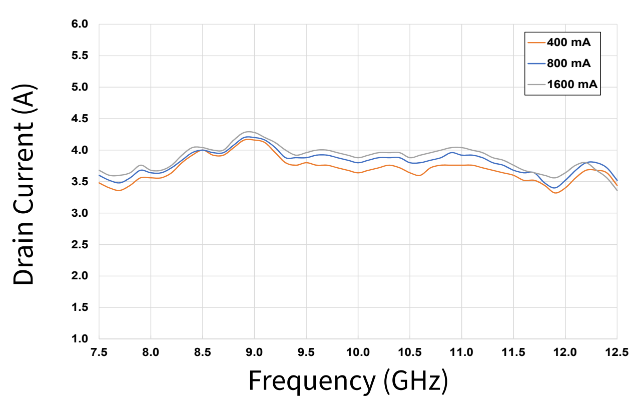


Figure 12. Drain Current vs Frequency as a Function of IDQ



Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, PW = 100 us, DC = 10%, Pin = 26 dBm, T_{BASE} = +25 °C

Figure 13. Output Power vs Input Power as a Function of Frequency

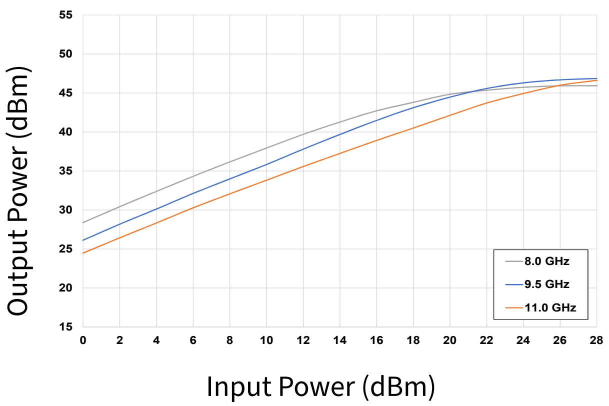


Figure 14. Power Added Eff. vs Input Power as a Function of Frequency

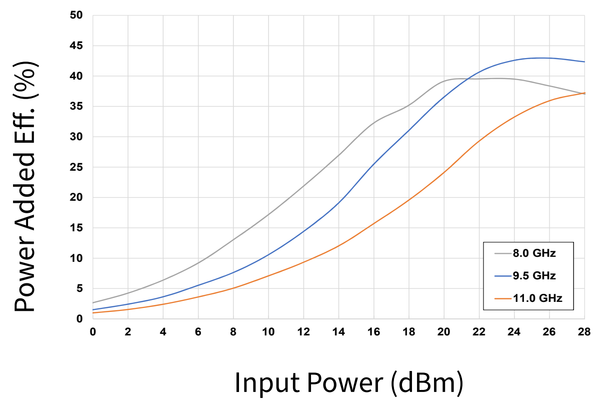


Figure 15. Large Signal Gain vs Input Power as a Function of Frequency

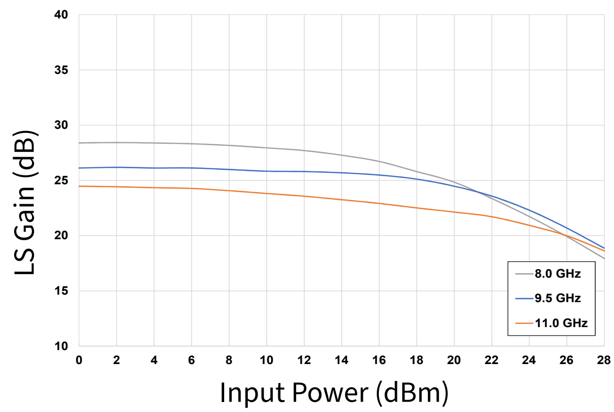


Figure 16. Drain Current vs Input Power as a Function of Frequency

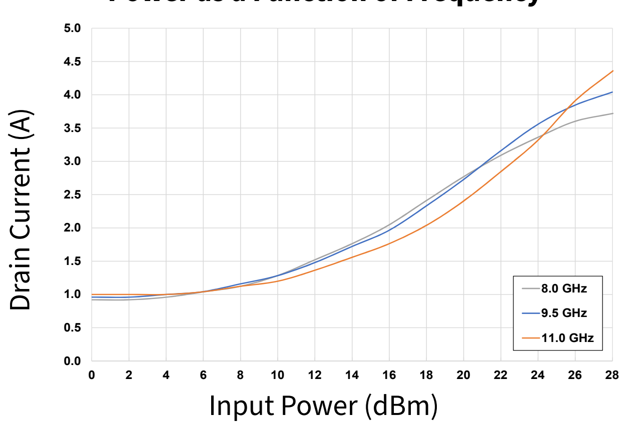
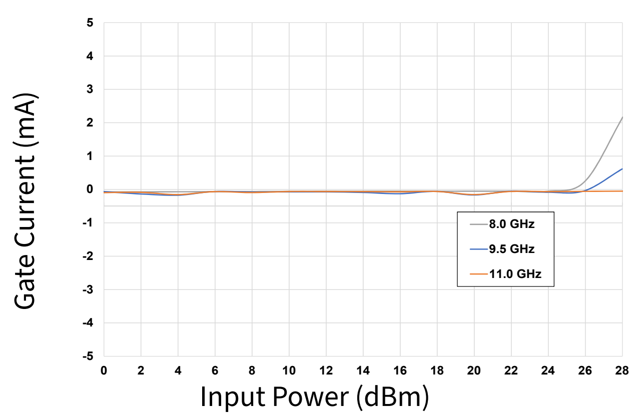


Figure 17. Gate Current vs Input Power as a Function of Frequency



Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, PW = 100 us, DC = 10%, Pin = 26 dBm, T_{BASE} = +25 °C

Figure 18. Output Power vs Input Power as a Function of Temperature

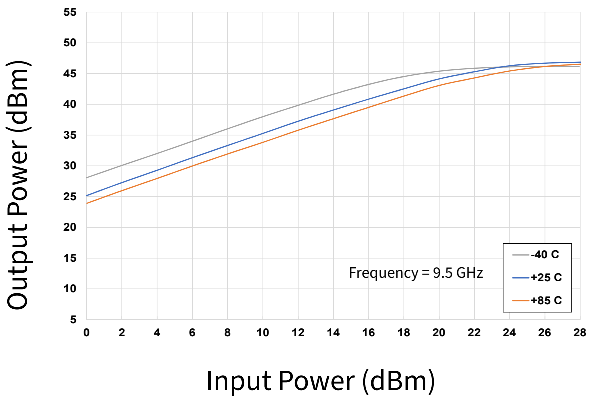


Figure 19. Power Added Eff. vs Input Power as a Function of Temperature

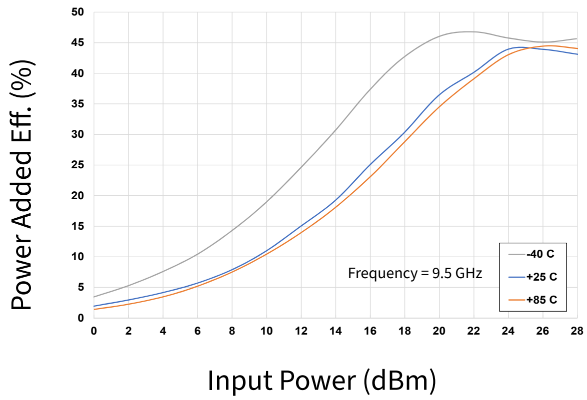


Figure 20. Large Signal Gain vs Input Power as a Function of Temperature

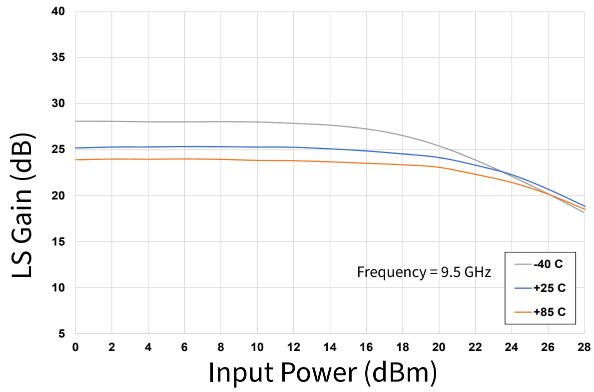


Figure 21. Drain Current vs Input Power as a Function of Temperature

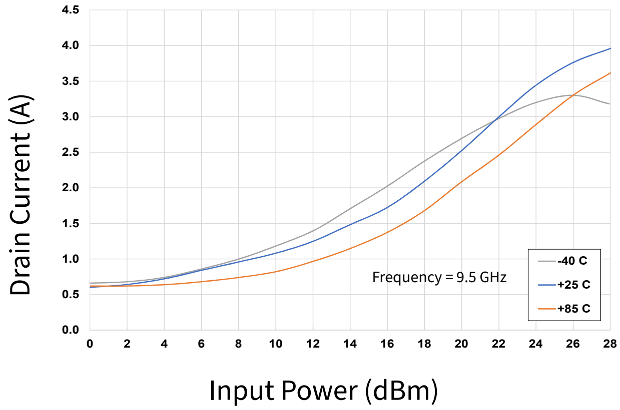
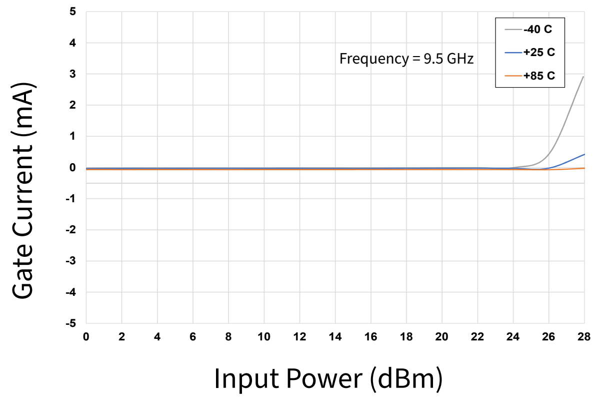


Figure 22. Gate Current vs Input Power as a Function of Temperature



Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, PW = 100 us, DC = 10%, Pin = 26 dBm, T_{BASE} = +25 °C

Figure 23. Output Power vs Input Power as a Function of IDQ

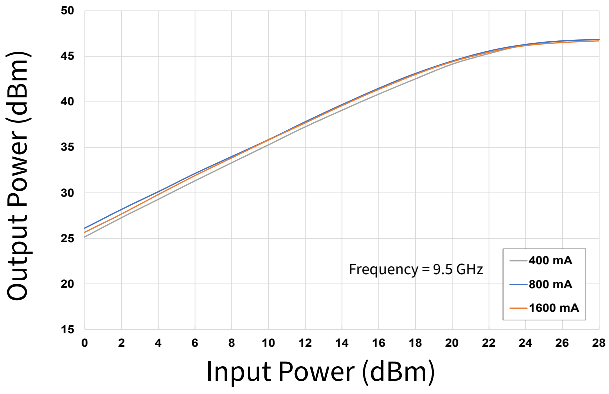


Figure 24. Power Added Eff. vs Input Power as a Function of IDQ

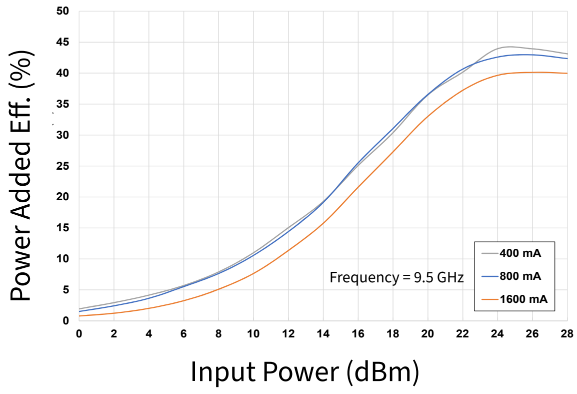


Figure 25. Large Signal Gain vs Input Power as a Function of IDQ

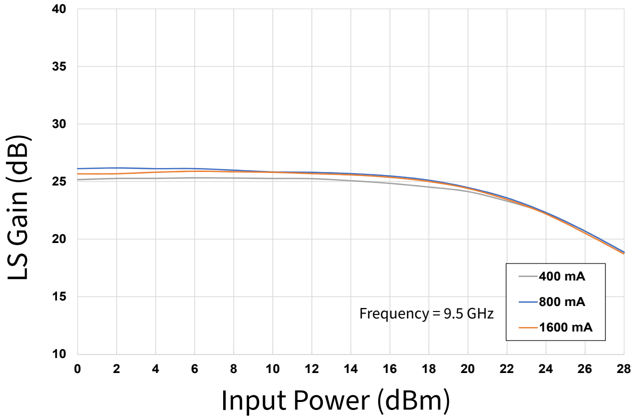


Figure 26. Drain Current vs Input Power as a Function of IDQ

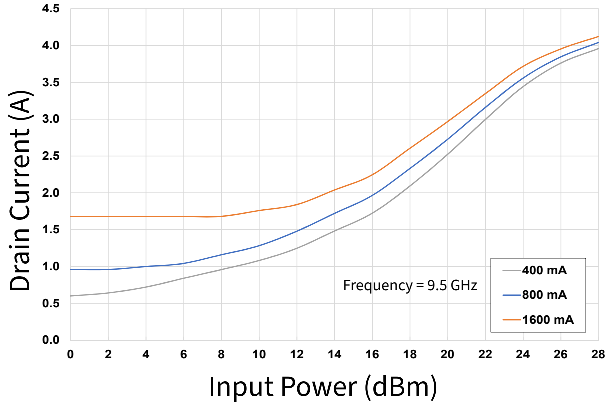
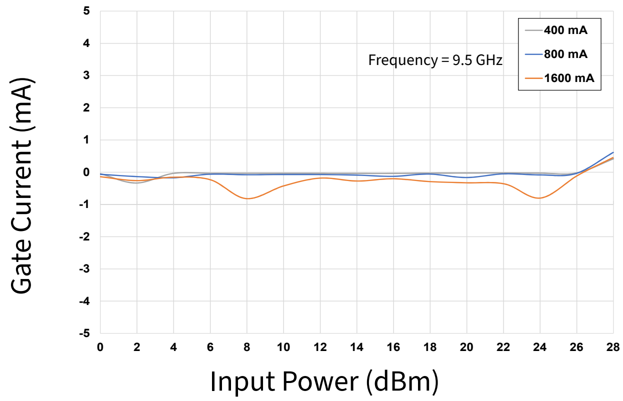


Figure 27. Gate Current vs Input Power as a Function of IDQ



Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, PW = 100 us, DC = 10%, Pin = 26 dBm, T_{BASE} = +25 °C

Figure 28. 2nd Harmonic vs Output Power as a Function of Frequency

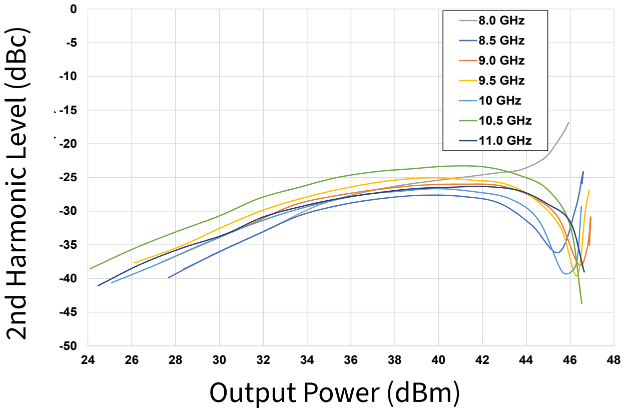


Figure 29. 3rd Harmonic vs Output Power as a Function of Frequency

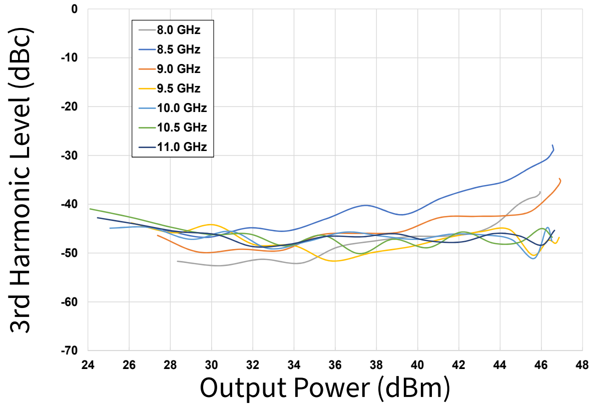


Figure 30. 2nd Harmonic vs Output Power as a Function of IDQ

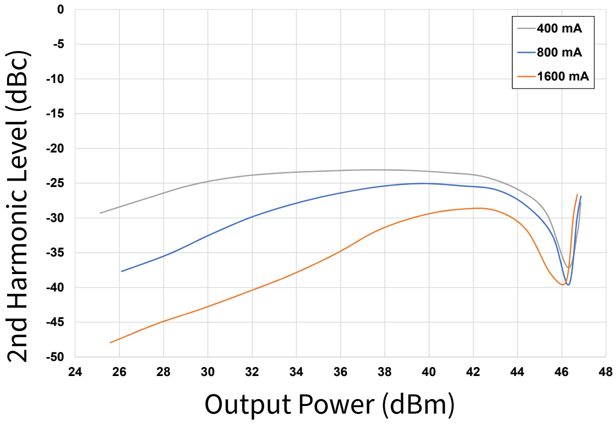
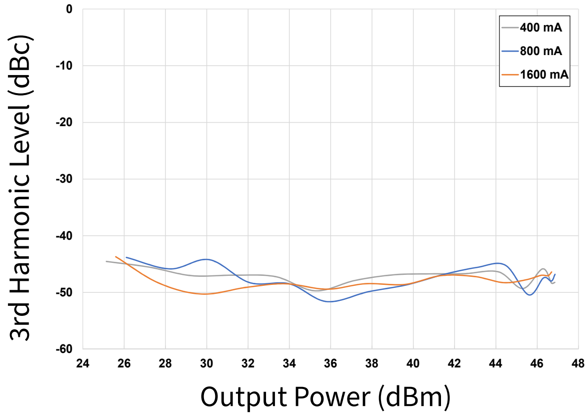


Figure 31. 3rd Harmonic vs Output Power as a Function of IDQ



Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, Pin = -20 dBm, T_{BASE} = +25 °C

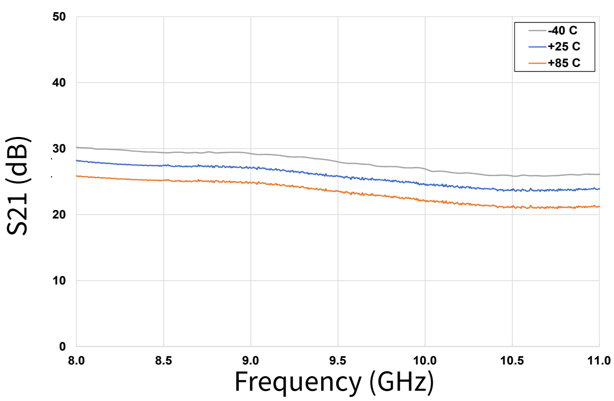


Figure 32. Gain vs Frequency as a Function of Temperature

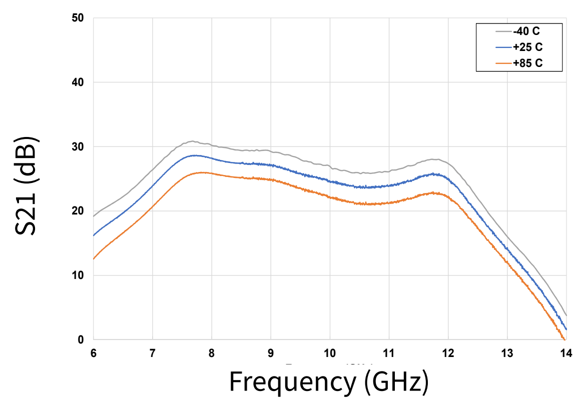


Figure 33. Gain vs Frequency as a Function of Temperature

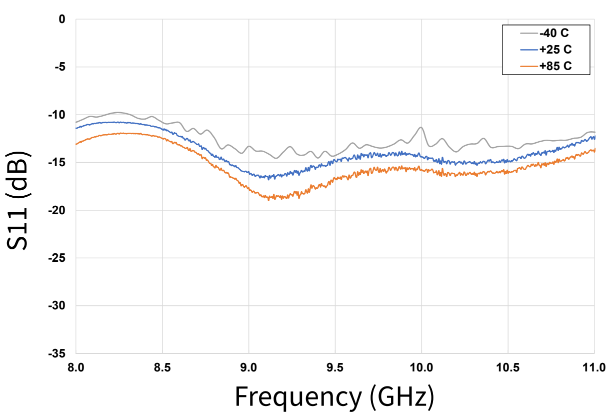


Figure 34. Input RL vs Frequency as a Function of Temperature

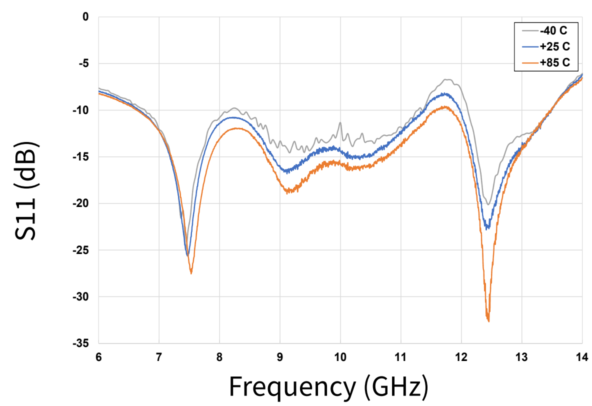


Figure 35. Input RL vs Frequency as a Function of Temperature

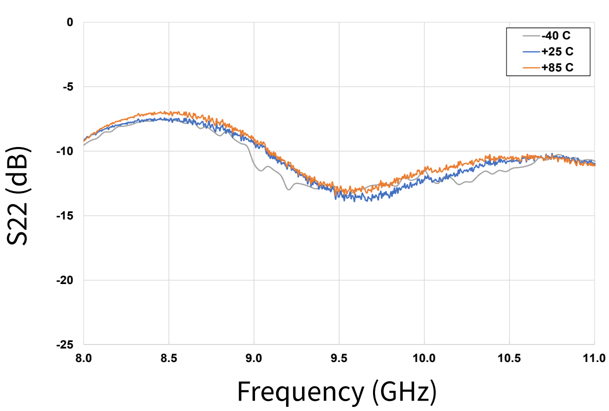


Figure 36. Output RL vs Frequency as a Function of Temperature

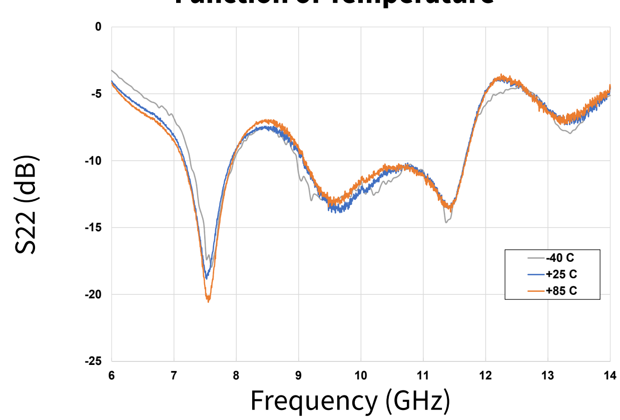


Figure 37. Output RL vs Frequency as a Function of Temperature

Typical Performance of the CMPA801B030S

Test conditions unless otherwise noted: V_D = 28 V, I_{DQ} = 800 mA, Pin = -20 dBm, T_{BASE} = +25 °C

Figure 38. Gain vs Frequency as a Function of Voltage

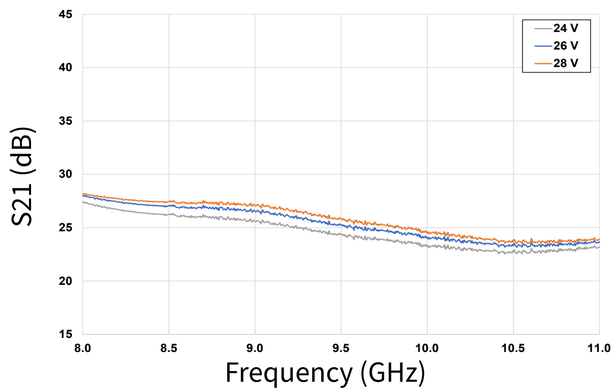


Figure 39. Gain vs Frequency as a Function of IDQ

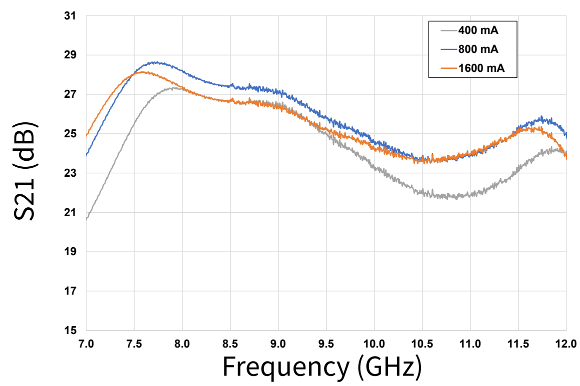


Figure 40. Input RL vs Frequency as a Function Voltage

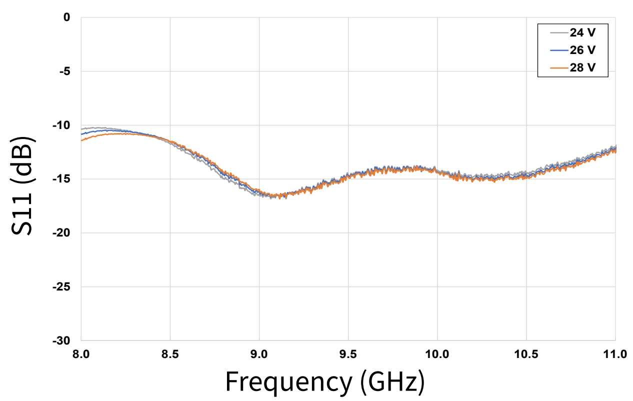


Figure 41. Input RL vs Frequency as a Function of IDQ

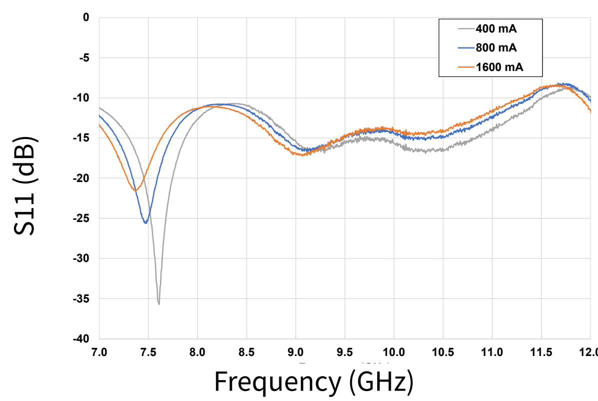


Figure 42. Output RL vs Frequency as a Function of Voltage

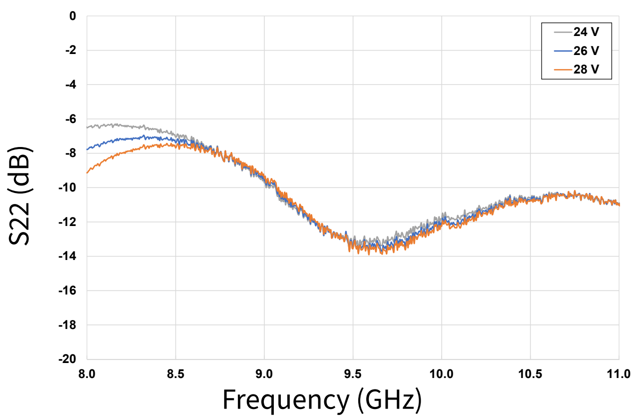
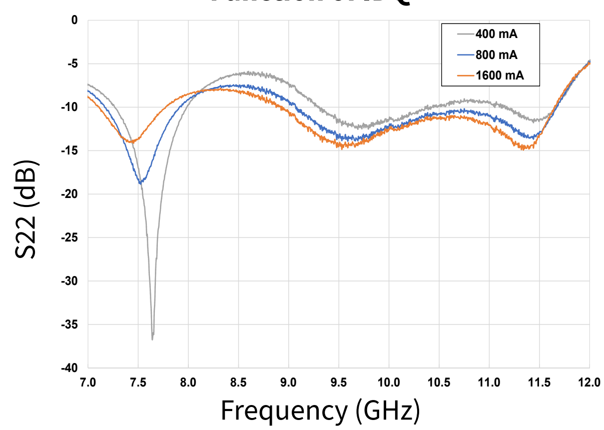
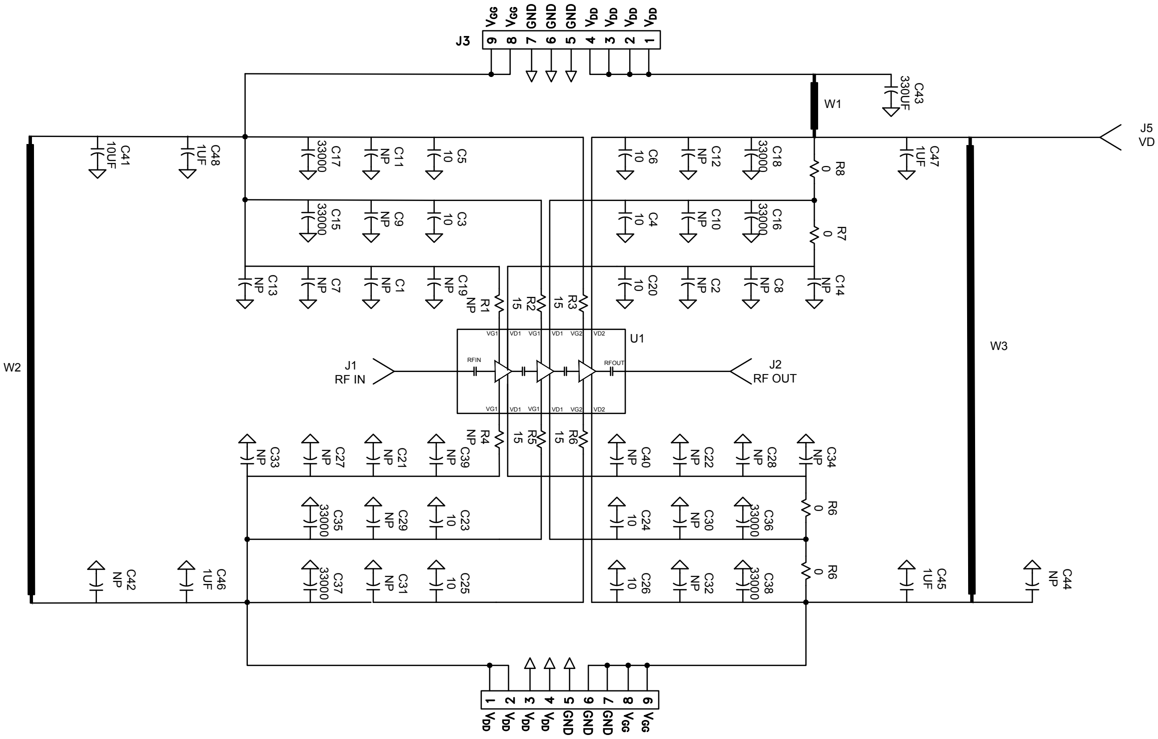


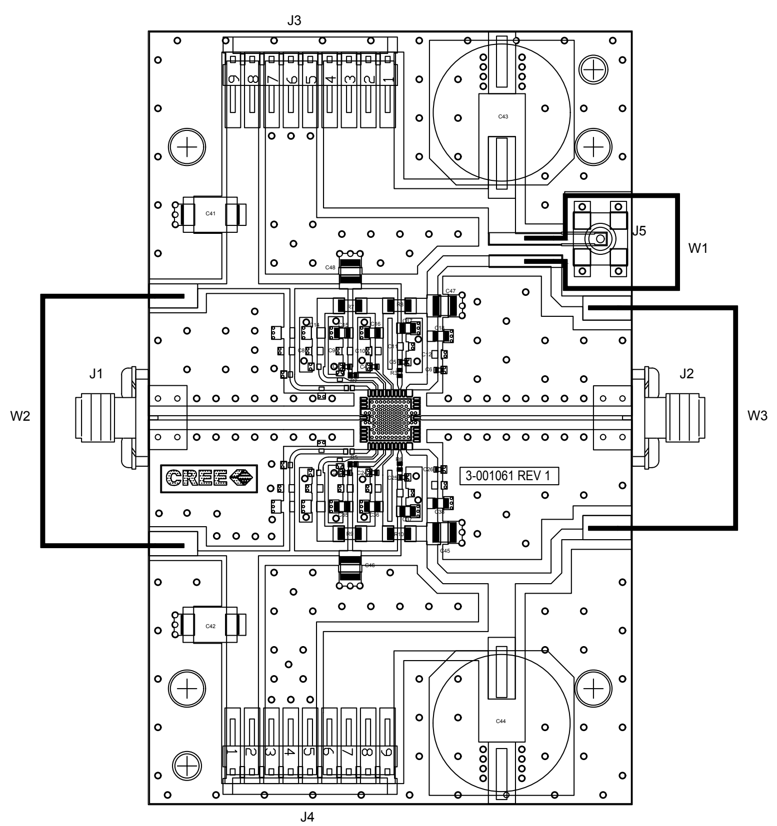
Figure 43. Output RL vs Frequency as a Function of IDQ



CMPA801B030S-AMP1 Application Circuit



CMPA801B030S-AMP1 Evaluation Board Layout



CMPA801B030S-AMP1 Evaluation Board Bill of Materials

Designator	Description	Qty
C3, C4, C5, C6, C23, C24, C25, C26	CAP, 10pF, +/-5%, pF, 200V, 0402	8
C15, C16, C17, C18, C35, C36, C37, C38	CA, 330000PF, 0805,100V, X7R	8
C45, C46, C47, C48	CAP, 1.0UF, 100V, 10%, X7R, 1210	4
C41	CAP 10UF 16V TANTALUM, 2312	1
C43	CAP, 330 UF, +/-20%, 100V, ELECTROLYTIC, CASE SIZE K16	1
R2, R3, R5, R6	RES 15 OHM, +/-1%, 1/16W, 0402	6
R8, R10	RES 0.0 OHM 1/16W 1206 SMD	2
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST, 20MIL	4
J5	CONN, SMB, STRAIGHT JACK RECEPTACLE, SMT, 50 OHM, Au PLATED	1
J3, J4	HEADER RT>PLZ .1CEN LK 9POS	1
W2, W3	WIRE, BLACK, 20 AWG ~ 2.5”	2
W1	WIRE, BLACK, 20 AWG ~ 3.0”	1
	PCB, TEST FIXTURE, RF-35TC, 0.010 THK, 7X7 Overmold QFN SOCKET BOARD	1
	2-56 SOC HD SCREW 3/16 SS	4
	#2 SPLIT LOCKWASHER SS	4
Q1	CMPA801B030S	1

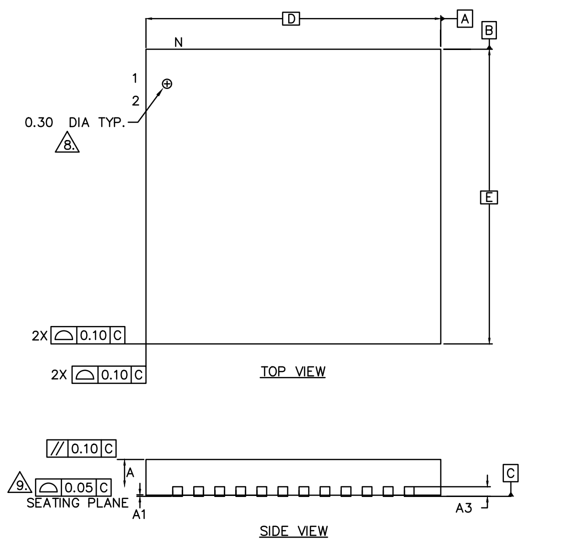
Electrostatic Discharge (ESD) Classifications

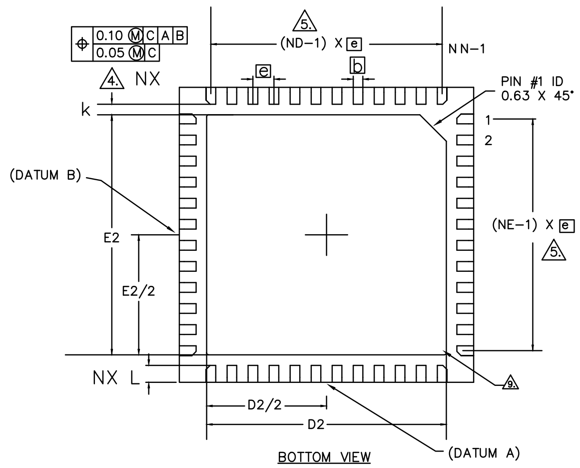
Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1B (≥ 500 V)	JEDEC JESD22 A114-D
Charge Device Model	CDM	II (≥ 200 V)	JEDEC JESD22 C101-C

Moisture Sensitivity Level (MSL) Classification

Parameter	Symbol	Level	Test Methodology
Moisture Sensitivity Level	MSL	3 (168 hours)	IPC/JEDEC J-STD-20

Product Dimensions CMPA801B030S (Package 7 x 7 QFN)



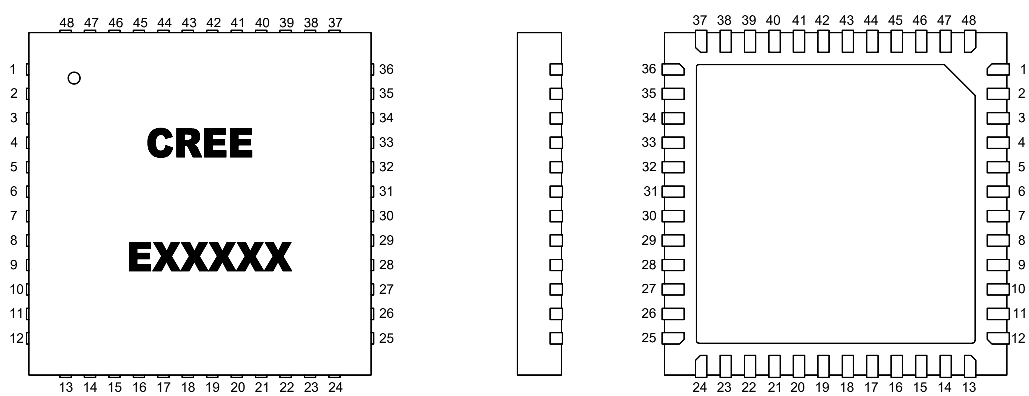


NOTES :

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M. – 1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS, θ IS IN DEGREES.
3. N IS THE TOTAL NUMBER OF TERMINALS.
4. DIMENSION b APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM TERMINAL TIP.
5. ND AND NE REFER TO THE NUMBER OF TERMINALS ON EACH D AND E SIDE RESPECTIVELY.
6. MAX. PACKAGE WARPAGE IS 0.05 mm.
7. MAXIMUM ALLOWABLE BURRS IS 0.076 mm IN ALL DIRECTIONS.
8. PIN #1 ID ON TOP WILL BE LASER MARKED.
9. BILATERAL COPLANARITY ZONE APPLIES TO THE EXPOSED HEAT SINK SLUG AS WELL AS THE TERMINALS.
10. THIS DRAWING CONFORMS TO JEDEC REGISTERED OUTLINE MO–220
11. ALL PLATED SURFACES ARE TIN 0.010 mm +/– 0.005mm.

SYMBOL	MIN.	NOM.	MAX.	NOTE
A	0.80	0.9	1.0	
A1	0.00	0.03	0.06	
A3		0.20 REF.		
θ	0	—	12	2
K		0.20 MIN.		
D		7.0 BSC		
E		7.0 BSC		

SYMBOL	0.50mm LEAD PITCH			NOTE
	MIN.	NOM.	MAX.	
e		0.50 BSC.		
N		48		3
ND		12		5
NE		12		5
L	0.35	0.41	0.46	
b	0.19	0.25	0.33	4
D2	5.61	5.72	5.83	
E2	5.61	5.72	5.83	



PIN	DESC.	PIN	DESC.	PIN	DESC.	PIN	DESC.
1	NC	15	NC	29	NC	43	NC
2	NC	16	NC	30	RFGND	44	VG1B
3	NC	17	VG1A	31	RFOUT	45	NC
4	NC	18	NC	32	RFGND	46	NC
5	RFGND	19	VD1A	33	NC	47	NC
6	RFIN	20	NC	34	NC	48	NC
7	RFGND	21	VG2A	35	NC		
8	NC	22	NC	36	NC		
9	NC	23	VD2A	37	NC		
10	NC	24	NC	38	VD2B		
11	NC	25	NC	39	NC		
12	NC	26	NC	40	VG2B		
13	NC	27	NC	41	NC		
14	NC	28	NC	42	VD1B		

Part Number System

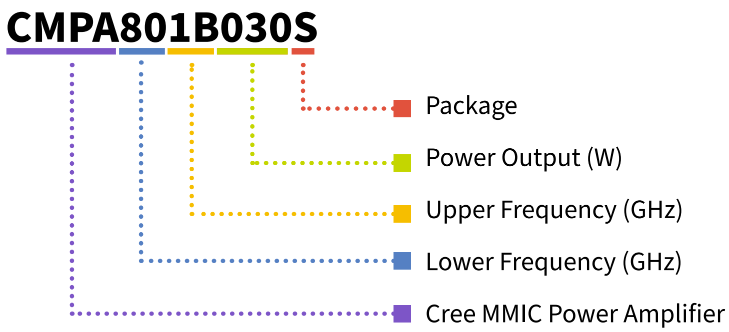


Table 1.

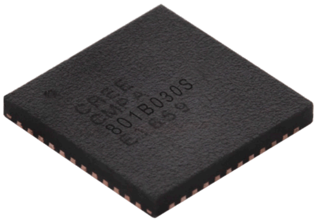
Parameter	Value	Units
Lower Frequency	7.9	GHz
Upper Frequency	11.0	GHz
Power Output	40	W
Package	Surface Mount	-

Note[1]: Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Table 2.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples:	1A = 10.0 GHz 2H = 27.0 GHz

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CMPA801B030S	Packaged GaN MMIC PA	Each	
CMPA801B030S-AMP1	Evaluation Board with GaN MMIC Installed	Each	

For more information, please contact:

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Notes & Disclaimer

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